DATA SHEET

TEA1067
Low voltage versatile telephone transmission circuit with dialler interface

Product specification
File under Integrated Circuits, IC03A

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Philips Semiconductors

PHILIPS

GENERAL DESCRIPTION

The TEA1067 is a bipolar integrated circuit performing all speech and line interface functions required in fully electronic telephone sets. It performs electronic switching between dialling and speech. The circuit is able to operate down to a DC line voltage of 1.6 V (with reduced performance) to facilitate the use of more telephone sets in parallel.

Features

- Low DC line voltage; operates down to 1.6 V (excluding polarity guard)
- Voltage regulator with adjustable static resistance
- Provides supply with limited current for external circuitry
- Symmetrical high-impedance inputs (64 kΩ) for dynamic, magnetic or piezoelectric microphones
- Asymmetrical high-impedance input (32 kΩ) for electret microphone
- DTMF signal input with confidence tone
- Mute input for pulse or DTMF dialling
- Power down input for pulse dial or register recall
- Receiving amplifier for magnetic, dynamic or piezoelectric earpieces
- Large gain setting range on microphone and earpiece amplifiers
- Line current dependent line loss compensation facility for microphone and earpiece amplifiers
- Gain control adaptable to exchange supply
- DC line voltage adjustment capability

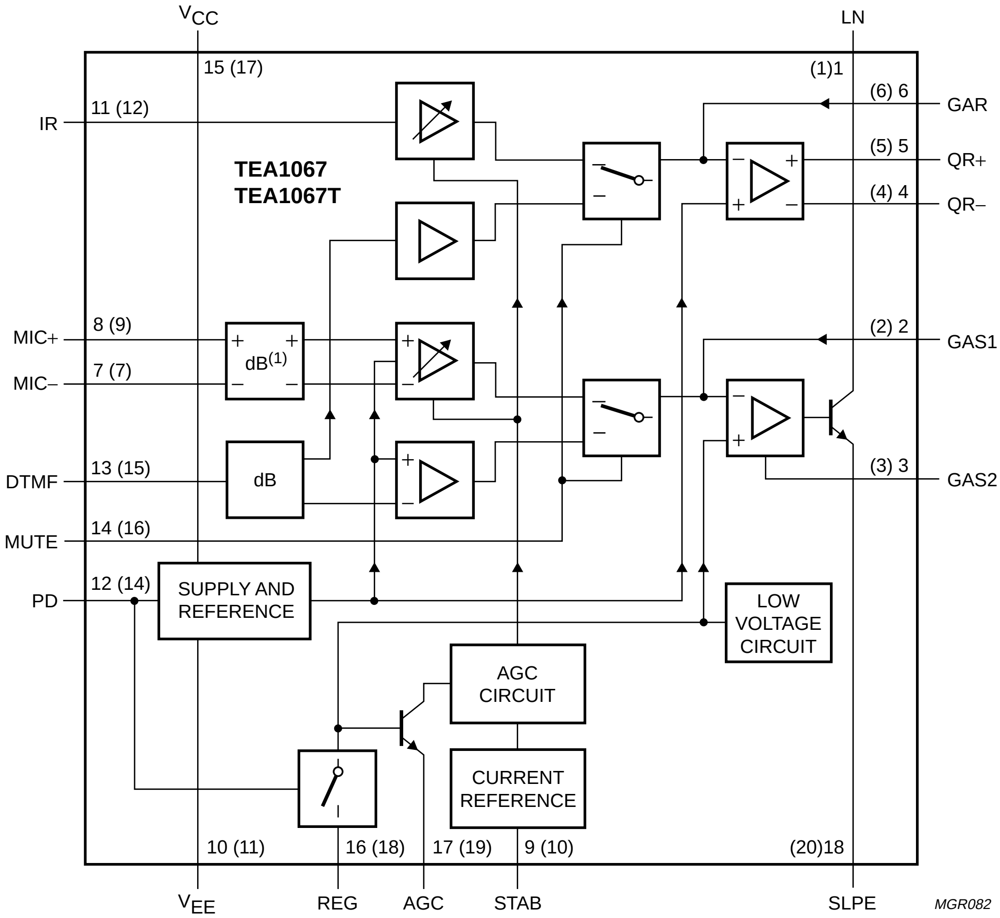
QUICK REFERENCE DATA

PARAMETER	CONDITIONS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Line voltage	I_{line} = 15 mA	V_{LN}	3.65	3.9	4.15	V
Line current operating range	normal operation					
	TEA1067	I_{line}	11	–	140	mA
	TEA1067T	I_{line}	11	–	140	mA
	with reduced performance	I_{line}	1	–	11	mA
Internal supply current	power down					
	input LOW	I_{CC}	–	1	1.35	mA
	input HIGH	I_{CC}	–	55	82	µA
Supply voltage for peripherals	I_{line} = 15 mA; I_p = 1.4 mA;					
	mute input HIGH	V_{CC}	2.2	2.4	–	V
	I_{line} = 15 mA; I_p = 0.9 mA;					
	mute input HIGH	V_{CC}	2.5	–	–	V
Voltage gain range						
microphone amplifier		G_v	44	–	52	dB
receiving amplifier		G_v	20	–	45	dB
Line loss compensation						
gain control range		ΔG_v	5.5	5.9	6.3	dB
Exchange supply voltage range		V_{exch}	36	–	60	V
Exchange feeding bridge						
resistance range		R_{exch}	0.4	–	1	kΩ

PACKAGE OUTLINES

TEA1067: 18-lead DIL; plastic (SOT102). SOT102-1; 1998 Jun 18.

TEA1067T: 20-lead mini-pack; plastic (SO20; SOT163A). SOT163-1; 1998 Jun 18.



Figures in parenthesis refer to TEA1067T.

Fig.1 Block diagram.

PINNING

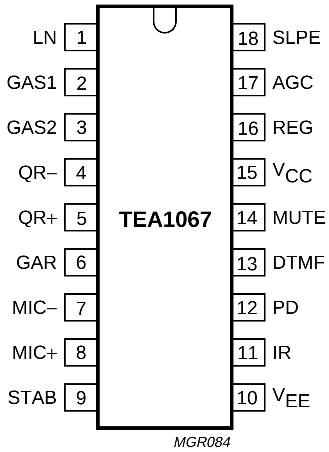


Fig.2 Pinning diagram for TEA1067 18-lead DIL version.

1	LN	positive line terminal
2	GAS1	gain adjustment; transmitting amplifier
3	GAS2	gain adjustment; transmitting amplifier
4	QR–	inverting output; receiving amplifier
5	QR+	non-inverting output receiving amplifier
6	GAR	gain adjustment; receiving amplifier
7	MIC–	inverting microphone input
8	MIC+	non-inverting microphone input
9	STAB	current stabilizer
10	V_{EE}	negative line terminal
11	IR	receiving amplifier input
12	PD	power-down input
13	DTMF	dual-tone multi-frequency input
14	MUTE	mute input
15	V_{CC}	positive supply decoupling
16	REG	voltage regulator decoupling
17	AGC	automatic gain control input
18	SLPE	slope (DC resistance) adjustment

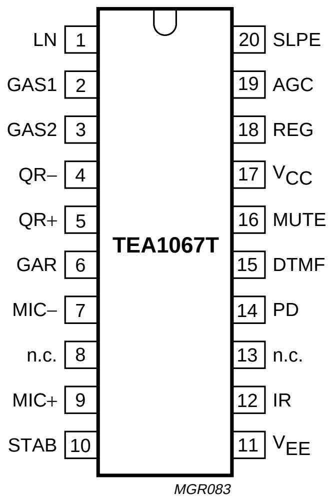


Fig.3 Pinning diagram for TEA1067T 20-lead mini-pack version.

1	LN	positive line terminal
2	GAS1	gain adjustment; transmitting amplifier
3	GAS2	gain adjustment; transmitting amplifier
4	QR–	inverting output; receiving amplifier
5	QR+	non-inverting output receiving amplifier
6	GAR	gain adjustment, receiving amplifier
7	MIC–	inverting microphone input
8	n.c.	not connected
9	MIC+	non-inverting microphone input
10	STAB	current stabilizer
11	V_{EE}	negative line terminal
12	IR	receiving amplifier input
13	n.c.	not connected
14	PD	power-down input
15	DTMF	dual-tone multi-frequency input
16	MUTE	mute input
17	V_{CC}	positive supply decoupling
18	REG	voltage regulator decoupling
19	AGC	automatic gain control input
20	SLPE	slope (DC resistance) adjustment

FUNCTIONAL DESCRIPTION

Supply: V_{CC}, LN, SLPE, REG and STAB

Power for the TEA1067 and its peripheral circuits is usually obtained from the telephone line. The IC develops its own supply at V_{CC} and regulates its voltage drop. The supply voltage V_{CC} may also be used to supply external circuits e.g. dialling and control circuits.

Decoupling of the supply voltage is performed by a capacitor between V_{CC} and V_{EE} while the internal voltage regulator is decoupled by a capacitor between REG and V_{EE}.

The DC current drawn by the device will vary in accordance with varying values of the exchange voltage (V_{exch}), the feeding bridge resistance (R_{exch}), and the DC resistance of the telephone line (R_{line}).

The TEA1067 has an internal current stabilizer working at a level determined by a 3.6 kΩ resistor connected between STAB and V_{EE} (see Fig.7). When the line current (I_{line}) is more than 0.5 mA greater than the sum of the IC supply current (I_{CC}) and the current drawn by the peripheral circuitry connected to V_{CC} (I_p) the excess current is shunted to V_{EE} via LN.
The regulated voltage on the line terminal (V_{LN}) can be calculated as:

$V_{LN} = V_{ref} + I_{SLPE} \times R9$; or
$V_{LN} = V_{ref} + [(I_{line} - I_{CC} - 0.5 \times 10^{-3}\ A) - I_p] \times R9$

Where V_{ref} is an internally generated temperature compensated reference voltage of 3.6 V and R9 is an external resistor connected between SLPE and V_{EE}.

In normal use the value of R9 would be 20 Ω. Changing the value of R9 will also affect microphone gain, DTMF gain, gain control characteristics, side-tone level and maximum output swing on LN, and the DC characteristics (especially at the lower voltages).

Under normal conditions, when $I_{SLPE} >> I_{CC} + 0.5\ mA + I_p$, the static behaviour of the circuit is that of a 3.6 V regulator diode with an internal resistance equal to that of R9. In the audio frequency range the dynamic impedance is largely determined by R1. Fig.4 shows the equivalent impedance of the circuit.

At line currents below 9 mA the internal reference voltage is automatically adjusted to a lower value (typically 1.6 V at 1 mA). This means that the operation of more sets in parallel is possible with DC line voltages (excluding the polarity guard) down to an absolute minimum voltage of 1.6 V. With line currents below 9 mA the circuit has limited sending and receiving levels. The internal reference voltage can be adjusted by means of an external resistor (R_{VA}). This resistor connected between LN and REG will decrease the internal reference voltage, connected between REG and SLPE it will increase the internal reference voltage.

Current (I_p) available from V_{CC} for peripheral circuits depends on the external components used. Fig.10 shows this current for V_{CC} > 2.2 V. If MUTE is LOW when the receiving amplifier is driven the available current is further reduced. Current availability can be increased by connecting the supply IC (TEA1081) in parallel with R1, as shown in Fig.17 (c), or by increasing the DC line voltage by means of an external resistor (R_{VA}) connected between REG and SLPE.

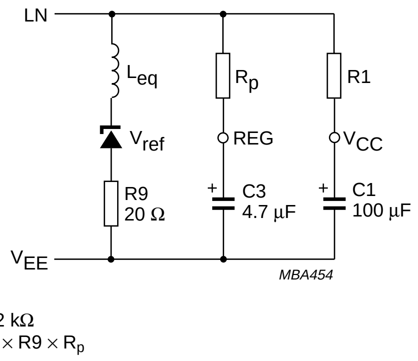


Fig.4 Equivalent impedance circuit.

Microphone inputs (MIC+ and MIC–) and gain adjustment pins (GAS1 and GAS2)

The TEA1067 has symmetrical microphone inputs. Its input impedance is 64 kΩ (2 × 32 kΩ) and its voltage gain is typically 52 dB (when R7 = 68 kΩ, see Fig.14). Dynamic, magnetic, piezoelectric or electret (with built-in FET source followers) microphones can be used. Microphone arrangements are shown in Fig.11.

The gain of the microphone amplifier can be adjusted between 44 dB and 52 dB to suit the sensitivity of the transducer in use. The gain is proportional to the value of R7 which is connected between GAS1 and GAS2. Stability is ensured by the external capacitor C6 which is connected between GAS1 and SLPE. The value of C6 is 100 pF but this may be increased to obtain a first-order low-pass filter. The cut-off frequency corresponds to the time constant R7 × C6.

Mute input (MUTE)

When MUTE is HIGH the DTMF input is enabled and the microphone and receiving amplifier inputs are inhibited. The reverse is true when MUTE is LOW or open-circuit. MUTE switching causes only negligible clicking on the earpiece outputs and line. If the number of parallel sets in use causes a drop in line current to below 6 mA the speech amplifiers remain active independent to the DC level applied to the MUTE input.

Dual-tone multi-frequency input (DTMF)

When the DTMF input is enabled dialling tones may be sent onto the line. The voltage gain from DTMF to LN is typically 25.5 dB (when R7 = 68 kΩ) and varies with R7 in the same way as the microphone gain. The signalling tones can be heard in the earpiece at a low level (confidence tone).

Receiving Amplifier (IR, QR+, QR– and GAR)

The receiving amplifier has one input (IR), one non-inverting complementary output (QR+) and an inverting complementary output (QR–). These outputs may be used for single-ended or differential drive depending on the sensitivity and type of earpiece used (see Fig.12). IR to QR + gain is typically 31 dB (when R4 = 100 kΩ), this is sufficient for low-impedance magnetic or dynamic microphones which are suited for single-ended drive. Using both outputs for differential drive gives an additional gain of 6 dB. This feature can be used when the earpiece impedance exceeds 450 Ω (high-impedance dynamic or piezoelectric types).

The receiving amplifier gain can be adjusted between 20 and 39 dB with single-ended drive and between 26 and 45 dB with differential drive, to match the sensitivity of the transducer in use. The gain is set with the value of R4 which is connected between GAR and QR+. Overall receive gain between LN and QR+ is calculated by substracting the anti-sidetone network attenuation (32 dB) from the amplifier gain. Two external capacitors C4 and C7, ensure stability. C4 is normally 100 pF and C7 is 10 × the value of C4. The value of C4 may be increased to obtain a first-order low-pass filter. The cut-off frequency will depend on the time constant R4 × C4.
The output voltage of the receiving amplifier is specified for continuous-wave drive. The maximum output voltage will be higher under speech conditions where the peak to RMS ratio is higher.

Automatic gain control input (AGC)

Automatic line loss compensation is achieved by connecting a resistor (R6) between AGC and V_{EE}. The automatic gain control varies the gain of the microphone amplifier and the receiving amplifier in accordance with the DC line current. The control range is 5.9 dB. This corresponds to a line length of 5 km for a 0.5 mm diameter copper twisted-pair cable with a DC resistance of 176 Ω/km and an average attenuation 1.2 dB/km. Resistor R6 should be chosen in accordance with the exchange supply voltage and its feeding bridge resistance (see Fig.13 and Table 1). The ratio of start and stop currents of the AGC curve is independent of the value of R6. If no automatic line loss compensation is required the AGC may be left open-circuit. The amplifiers, in this condition, will give their maximum specified gain.

Power-down input (PD)

During pulse dialling or register recall (timed loop break) the telephone line is interrupted. During these interruptions the telephone line provides no power for the transmission circuit or circuits supplied by V_{CC}. The charge held on C1 will bridge these gaps. This bridging is made easier by a HIGH level on the PD input which reduces the typical supply current from 1 mA to 55 μA and switches off the voltage regulator preventing discharge through LN. When PD is HIGH the capacitor at REG is disconnected with the effect that the voltage stabilizer will have no switch-on delay after line interruptions. This minimizes the contribution of the IC to the current waveform during pulse dialling or register recall. When this facility is not required PD may be left open-circuit.

Side-tone suppression

The anti-sidetone network, R1//Z_{line}, R2, R3, R9 and Z_{bal}, (see Fig.5) suppresses transmitted signal in the earpiece. Compensation is maximum when the following conditions are fulfilled:

(a) $R9 \times R2 = R1 (R3 + [R8//Z_{bal}])$;

(b) $(Z_{bal} / [Z_{bal} + R8]) = (Z_{line} / [Z_{line} + R1])$

If fixed values are chosen for R1, R2, R3, and R9 then condition (a) will always be fulfilled when $|R8//Z_{bal}| << R3$. To obtain optimum side-tone suppression condition (b) has to be fulfilled resulting in:

$Z_{bal} = (R8/R1)\ Z_{line} = k.Z_{line}$ where k is a scale factor; $k = (R8/R1)$

The scale factor (k), dependent on the value of R8, is chosen to meet the following criteria:

(a) Compatibility with a standard capacitor from the E6 or E12 range for Z_{bal}

(b) $|Z_{bal}//R8| << R3$ to fulfil condition (a) and thus ensuring correct anti-sidetone bridge operation

(c) $|Z_{bal} + R8| >> R9$ to avoid influencing the transmitter gain

In practice Z_{line} varies considerably with the line type and length. The value chosen for Z_{bal} should therefore be for an average line length thus giving optimum setting for short or long lines.

Example

The line balance impedance (Z_{bal}) at which the optimum suppression is present can be calculated by:
suppose Z_{line} = 210 Ω + (1265 Ω//140 nF), representing a 5 km line of 0.5 mm diameter, copper, twisted-pair cable matched to 600 Ω (176 Ω/km; 38 nF/km).
When k = 0.64 then R8 = 390 Ω;
Z_{bal} = 130 Ω + (820 Ω//220 nF).

The anti-sidetone network for the TEA1060 family shown in Fig.5 attenuates the signal received from the line by 32 dB before it enters the receiving amplifier. The attenuation is almost constant over the whole audio frequency range. Fig.6 shows a conventional Wheatstone bridge anti-sidetone circuit that can be used as an alternative. Both bridge types can be used with either resistive or complex set impedances.

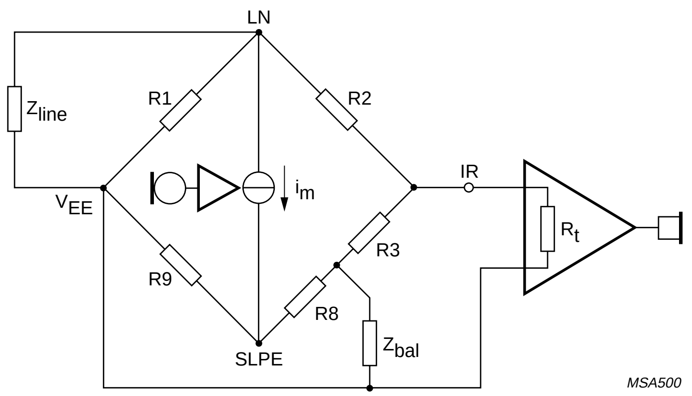


Fig.5 Equivalent circuit of TEA1060 anti-sidetone bridge.

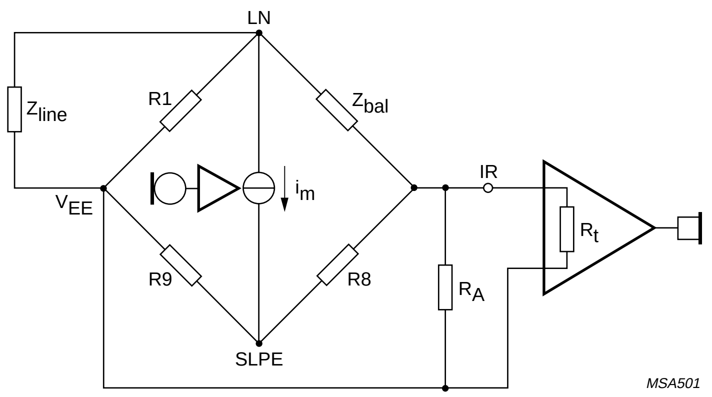


Fig.6 Equivalent circuit of an anti-sidetone network in a Wheatstone bridge configuration.

More information can be found in the designer guide; 9398 341 10011

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

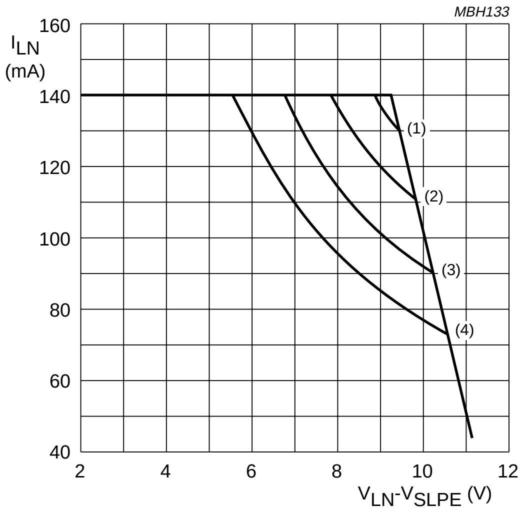
PARAMETER	CONDITIONS	SYMBOL	MIN.	MAX.	UNIT
Positive continuous line voltage		V_{LN}	–	12	V
Repetitive line voltage during switch-on line interruption		V_{LN}	–	13.2	V
Repetitive peak line voltage for a 1 ms pulse per 5 s	R9 = 20 Ω; R10 = 13 Ω (Fig.16)	V_{LN}	–	28	V
Line current TEA1067 (note 1)	R9 = 20 Ω	I_{line}	–	140	mA
Line current TEA1067T (note 1)	R9 = 20 Ω	I_{line}	–	140	mA
Voltage on all other pins		V_i	–	V_{CC} + 0.7	V
		$-V_i$	–	0.7	V
Total power dissipation (note 2)	R9 = 20 Ω				
TEA1067		P_{tot}	–	769	mW
TEA1067T		P_{tot}	–	550	mW
Storage temperature range		T_{stg}	–40	+ 125	°C
Operating ambient temperature range		T_{amb}	–25	+ 75	°C
Junction temperature		T_j	–	+ 125	°C

Notes

1. Mostly dependent on the maximum required T_{amb} and on the voltage between LN and SLPE. See Figs 7 and 8 to determine the current as a function of the required voltage and the temperature.
2. Calculated for the maximum ambient temperature specified T_{amb} = 75 °C and a maximum junction temperature of 125 °C.

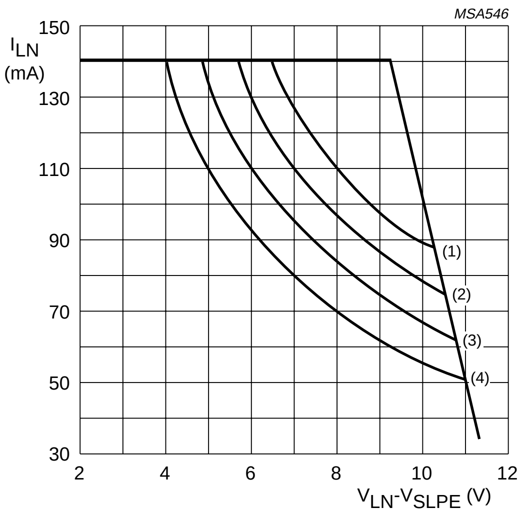
THERMAL RESISTANCE

From junction to ambient in free air				
TEA1067	$R_{th\ j\text{-}a}$	typ.	65	K/W
TEA1067T mounted on glass epoxy board 41 × 19 × 1.5 mm	$R_{th\ j\text{-}a}$	typ.	90	K/W



	T_{amb}	P_{tot}
(1)	45 °C	1231 mW
(2)	55 °C	1077 mW
(3)	65 °C	923 mW
(4)	75 °C	769 mW

Fig.7 TEA1067 safe operating area.



	T_{amb}	P_{tot}
(1)	45 °C	888 mW
(2)	55 °C	777 mW
(3)	65 °C	666 mW
(4)	75 °C	555 mW

Fig.8 TEA1067T safe operating area.

CHARACTERISTICS

I_{line} = 11 to 140 mA; V_{EE} = 0 V; f = 800 Hz; T_{amb} = 25 °C; unless otherwise specified

PARAMETER	CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply; LN and V_{CC}						
Voltage drop over circuit, between LN and V_{EE}	microphone inputs open					
	I_{line} = 1 mA	V_{LN}	–	1.6	–	V
	I_{line} = 4 mA	V_{LN}	1.75	2.0	2.25	V
	I_{line} = 7 mA	V_{LN}	2.25	2.8	3.35	V
	I_{line} = 11 mA	V_{LN}	3.55	3.8	4.05	V
	I_{line} = 15 mA	V_{LN}	3.65	3.9	4.15	V
	I_{line} = 100 mA	V_{LN}	4.9	5.6	6.5	V
	I_{line} = 140 mA	V_{LN}	–	–	7.5	V
Variation with temperature	I_{line} = 15 mA	$\Delta V_{LN}/\Delta T$	–3	–1	1	mV/K
Voltage drop over circuit, between LN and V_{EE} with external resistor R_{VA}	I_{line} = 15 mA; R_{VA} (LN to REG) = 68 kΩ		3.1	3.4	3.7	V
	I_{line} = 15 mA; R_{VA} (REG to SLPE) = 39 kΩ		4.2	4.5	4.8	V
Supply current	PD = LOW; V_{CC} = 2.8 V	I_{CC}	–	1.0	1.35	mA
Supply current	PD = HIGH; V_{CC} = 2.8 V	I_{CC}	–	55	82	µA
Supply voltage available for peripheral circuitry	I_{line} = 15 mA; MUTE = HIGH					
	I_p = 1.4 mA	V_{CC}	2.2	2.4	–	V
	I_p = 0 mA	V_{CC}	2.95	3.2	–	V
Microphone inputs MIC+ and MIC–						
Input impedance (differential) between MIC– and MIC+		$\lvert Z_i \rvert$	51	64	77	kΩ
Input impedance (single-ended) MIC– or MIC+ to V_{EE}		$\lvert Z_i \rvert$	25.5	32	38.5	kΩ
Common mode rejection ratio		k_{CMR}	–	82	–	dB
Voltage gain MIC+/MIC– to LN	I_{line} = 15 mA; R7 = 68 kΩ	G_v	51	52	53	dB

PARAMETER	CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Gain variation with frequency at f = 300 Hz and f = 3400 Hz	w.r.t 800 Hz	ΔG_{vf}	–0.5	± 0.2	+0.5	dB
Gain variation with temperature at –25 °C and + 75 °C	w.r.t. 25 °C without R6; I_{line} = 50 mA	ΔG_{vT}	–	± 0.2	–	dB
Dual-tone multi-frequency input DTMF						
Input impedance		$\lvert Z_i \rvert$	16.8	20.7	24.6	kΩ
Voltage gain from DTMF to LN	I_{line} = 15 mA; R7 = 68 kΩ	G_v	24.5	25.5	26.5	dB
Gain variation with frequency at f = 300 Hz and f = 3400 Hz	w.r.t. 800 Hz	ΔG_{vf}	–0.5	±0.2	+0.5	dB
Gain variation with temperature at –25 °C and +75 °C	w.r.t. 25 °C I_{line} = 50 mA	ΔG_{vT}	–	±0.2	–	dB
Gain adjustment GAS1 and GAS2						
Gain variation of the transmitting amplifier by varying R7 between GAS1 and GAS2		ΔG_v	–8	–	0	dB
Sending amplifier output LN						
Output voltage	I_{line} = 15 mA					
	THD = 2%	$V_{LN(rms)}$	–	1.9	–	V
	THD = 10%	$V_{LN(rms)}$	1.9	2.2	–	V
	I_{line} = 4 mA; THD = 10%	$V_{LN(rms)}$	–	0.8	–	V
	I_{line} = 7 mA; THD = 10%	$V_{LN(rms)}$	–	1.4	–	V
Noise output voltage	I_{line} = 15 mA; R7 = 68 kΩ; 200 Ω between MIC– and MIC+; psophometrically weighted (P53 curve)	$V_{no(rms)}$	–	–72	–	dBmp
Receiving amplifier input IR						
Input impedance		$\lvert Z_i \rvert$	17	21	25	kΩ

PARAMETER	CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Receiving amplifier outputs QR+ and QR–						
Output impedance (single-ended)		$\lvert Z_o \rvert$	–	4	–	Ω
Voltage gain from IR to QR+ or QR–	I_{line} = 15 mA R4 = 100 kΩ					
single-ended	R_L (from QR+ or QR–) = 300 Ω	G_v	30	31	32	dB
differential	R_L (from QR+ or QR–) = 600 Ω	G_v	36	37	38	dB
Gain variation with frequency at f = 300 Hz and f = 3400 Hz	w.r.t. 800 Hz	ΔG_{vf}	–0.5	–0.2	0	dB
Gain variation with temperature at –25 °C and +75 °C	w.r.t. 25 °C without R6; I_{line} = 50 mA	ΔG_{vT}	–	±0.2	–	dB
Output voltage	sinewave drive I_{line} = 15 mA; I_p = 0 mA; THD = 2% R4 = 100 kΩ					
single-ended	RL = 150 Ω	$V_{o(rms)}$	0.25	0.29	–	V
	RL = 450 Ω	$V_{o(rms)}$	0.45	0.55	–	V

differential	f = 3400 Hz;
	series R = 100 Ω;
	C_L = 47 nF
		$V_{o(rms)}$	0.65	0.80	–	V

Output voltage	THD = 10%; RL = 150 Ω R4 = 100 kΩ					
	I_{line} = 4 mA	$V_{o(rms)}$	–	15	–	mV
	I_{line} = 7 mA	$V_{o(rms)}$	–	130	–	mV
Noise output voltage	I_{line} = 15 mA; R4 = 100 kΩ; IR open-circuit psophometrically weighted; (P53 curve)					
single-ended	RL = 300 Ω	$V_{no(rms)}$	–	50	–	μV
differential	RL = 600 Ω	$V_{no(rms)}$	–	100	–	μV

PARAMETER	CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Gain adjustment GAR						
Gain variation of receiving amplifier achievable by varying R4 between GAR and QR		ΔG_v	–11	–	+8	dB
Mute input						
Input voltage HIGH		V_{IH}	1.5	–	V_{CC}	V
Input voltage LOW		V_{IL}	–	–	0.3	V
Input current		I_{MUTE}	–	8	15	μA
Gain reduction MIC+ or MIC– to LN	MUTE = HIGH	ΔG_v	–	70	–	dB
Voltage gain from DTMF to QR+ or QR–	MUTE = HIGH; R4 = 100 kΩ; single-ended; R_L = 300 Ω	G_v	–21	–19	–17	dB
Power-down input PD						
Input voltage HIGH		V_{IH}	1.5	–	V_{CC}	V
Input voltage LOW		V_{IL}	–	–	0.3	V
Input current		I_{PD}	–	5	10	μA
Automatic gain control input AGC						
Controlling the gain from IR to QR+/QR– and the gain from MIC+/MIC– to LN; R6 between AGC and V_{EE}	R6 = 110 kΩ					
Gain control range	I_{line} = 70 mA	ΔG_v	–5.5	–5.9	–6.3	dB
Highest line current for maximum gain		I_{line}	–	23	–	mA
Minimum line current for minimum gain		I_{line}	–	61	–	mA
Reduction of gain between I_{line} = 15 mA and I_{line} = 35 mA		ΔG_v	–1.0	–1.5	–2.0	dB

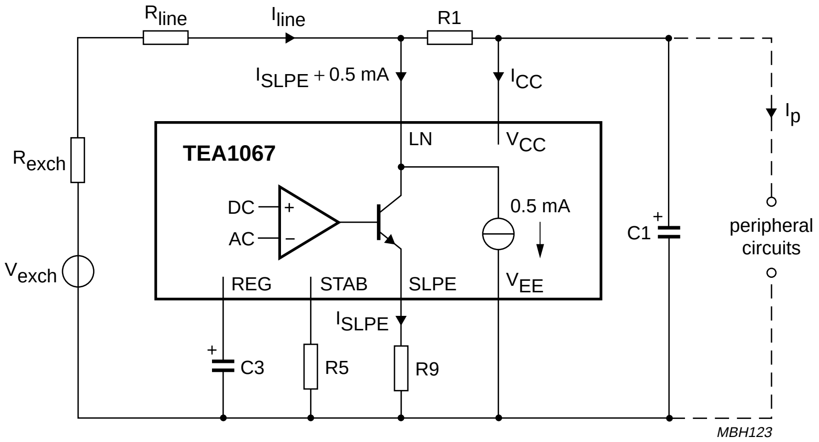
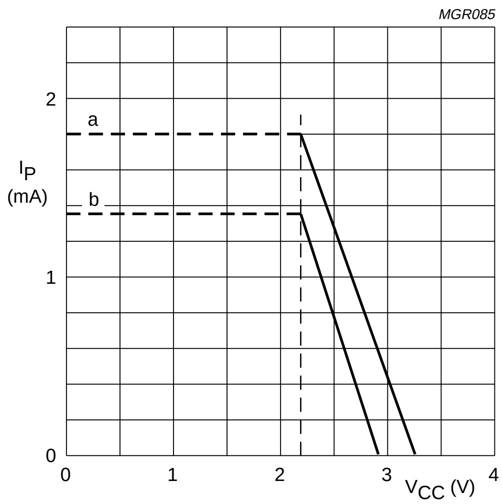


Fig.9 Supply arrangement.



Curve (a) is valid when the receiving amplifier is not driven or when MUTE = HIGH, curve (b) is valid when MUTE = LOW and the receiving amplifier is driven; $V_{o(rms)}$ = 150 mV, R_L = 150 Ω asymmetrical. The supply possibilities can be increased simply by setting the voltage drop over the circuit V_{LN} to a higher value by means of resistor R_{VA} connected between REG and SLPE.

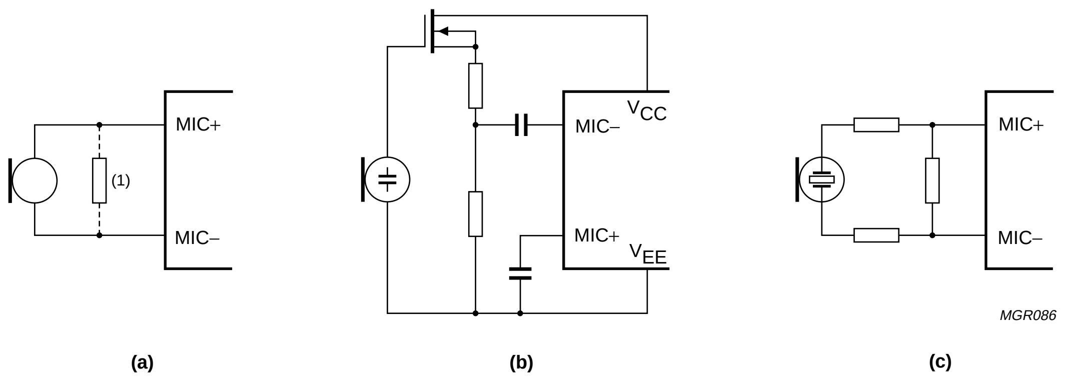
(a) I_p = 1.8 mA

(b) I_p = 1.35 mA

I_{line} = 15 mA at V_{LN} = 3.9 V

R1 = 620 Ω and R9 = 20 Ω.

Fig.10 Typical current I_p available from V_{CC} for peripheral circuitry with $V_{CC} \geq 2.2$ V.

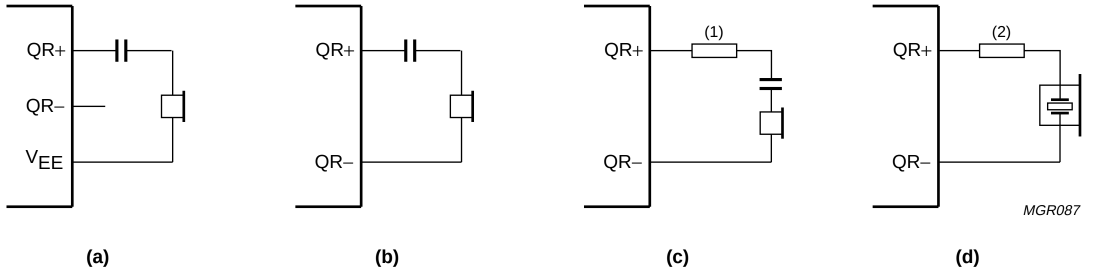


(a) Magnetic or dynamic microphone. The resistor marked (1) may be connected to decrease the terminating impedance.

(b) Electret microphone.

(c) Piezoelectric microphone.

Fig.11 Alternative microphone arrangements.



(a) Dynamic earpiece with less than 450 Ω impedance.

(b) Dynamic earpiece with more than 450 Ω impedance.

(c) Magnetic earpiece with more than 450 Ω impedance. The resistor marked (1) may be connected to prevent distortion (inductive load).

(d) Piezoelectric earpiece. The resistor marked (2) is required to increase the phase margin (capacitive load).

Fig.12 Alternative receiver arrangements.

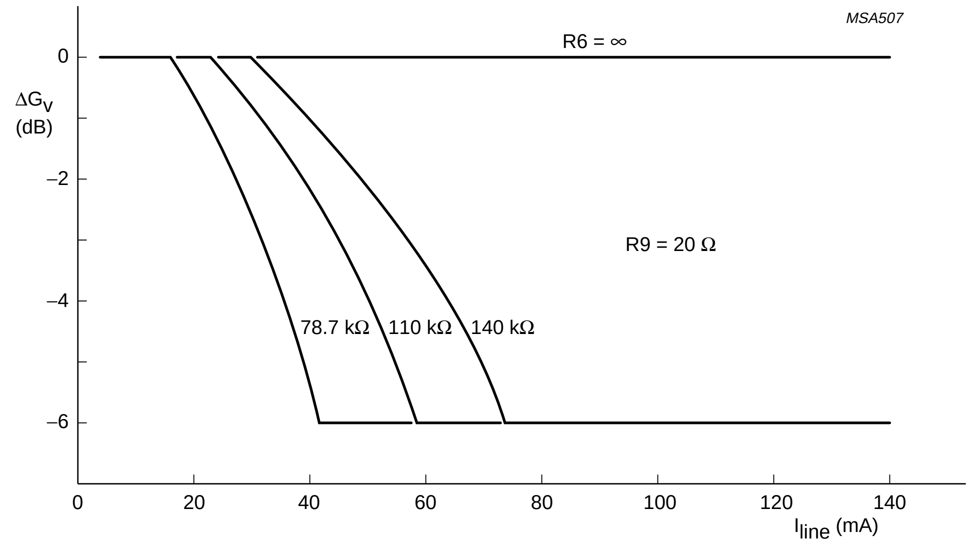
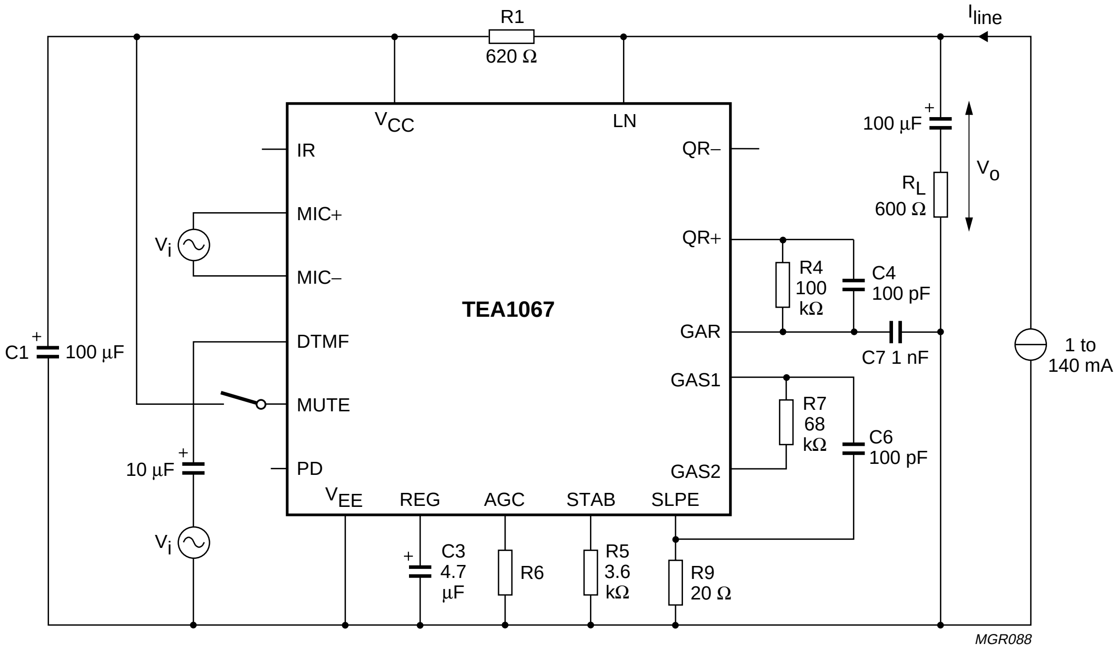


Fig.13 Variation of gain with line current, with R6 as a parameter.

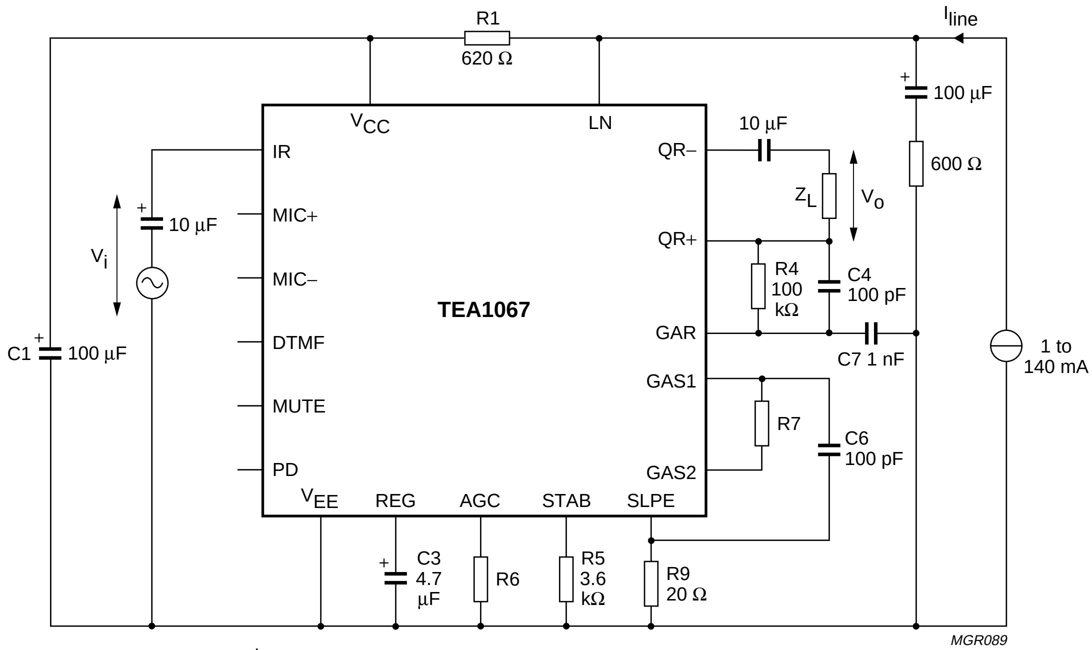
Table 1 Values of resistor R6 for optimum line loss compensation, for various usual values of exchange supply voltage (V_{exch}) and exchange feeding bridge resistance (R_{exch}); R9 = 20 Ω.

		R_{exch} (Ω)			
		400	600	800	1000
		R6 (kΩ)			
V_{exch} (V)	36	100	78.7	X	X
	48	140	110	93.1	82
	60	X	X	120	102



Voltage gain is defined as: $G_v = 20 \log |V_o/V_i|$. For measuring the gain from MIC+ and MIC– the MUTE input should be LOW or open, for measuring the DTMF input MUTE should be HIGH. Inputs not under test should be open.

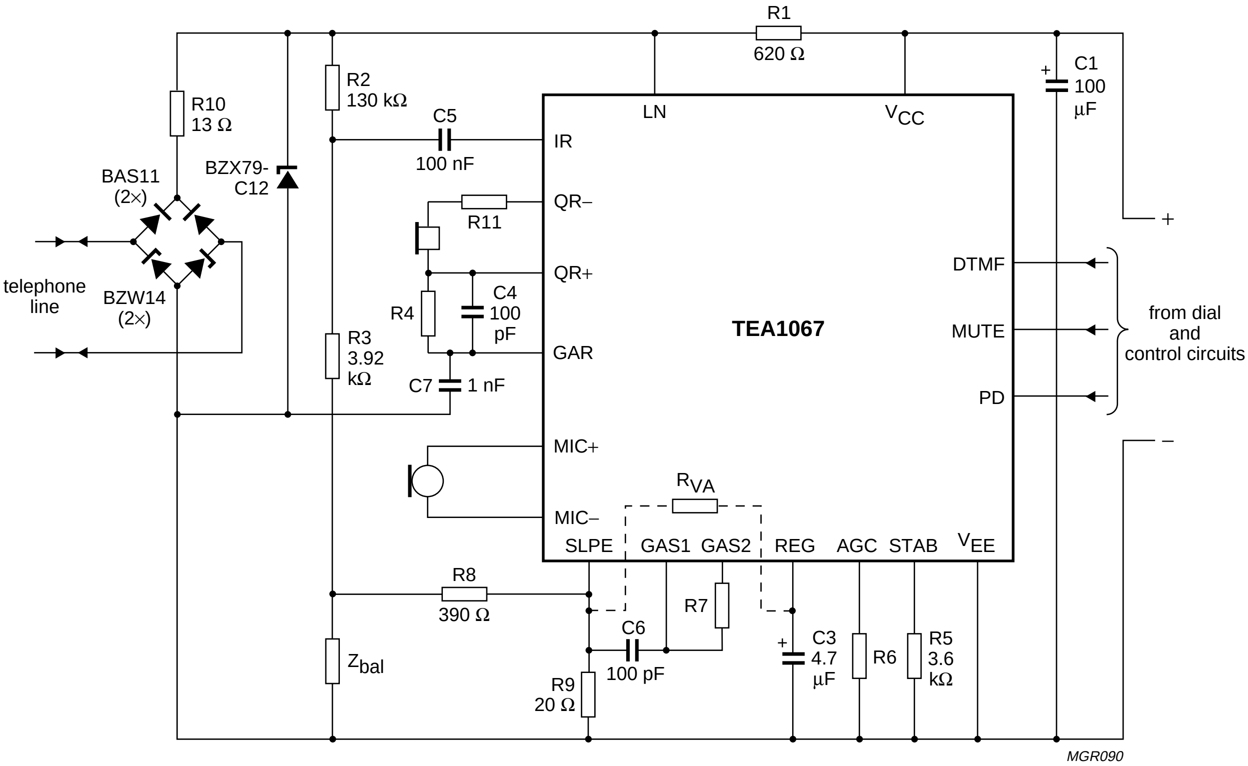
Fig.14 Test circuit for defining voltage gain of MIC+, MIC– and DTMF inputs.



Voltage gain is defined as: $G_v = 20 \log |V_o/V_i|$.

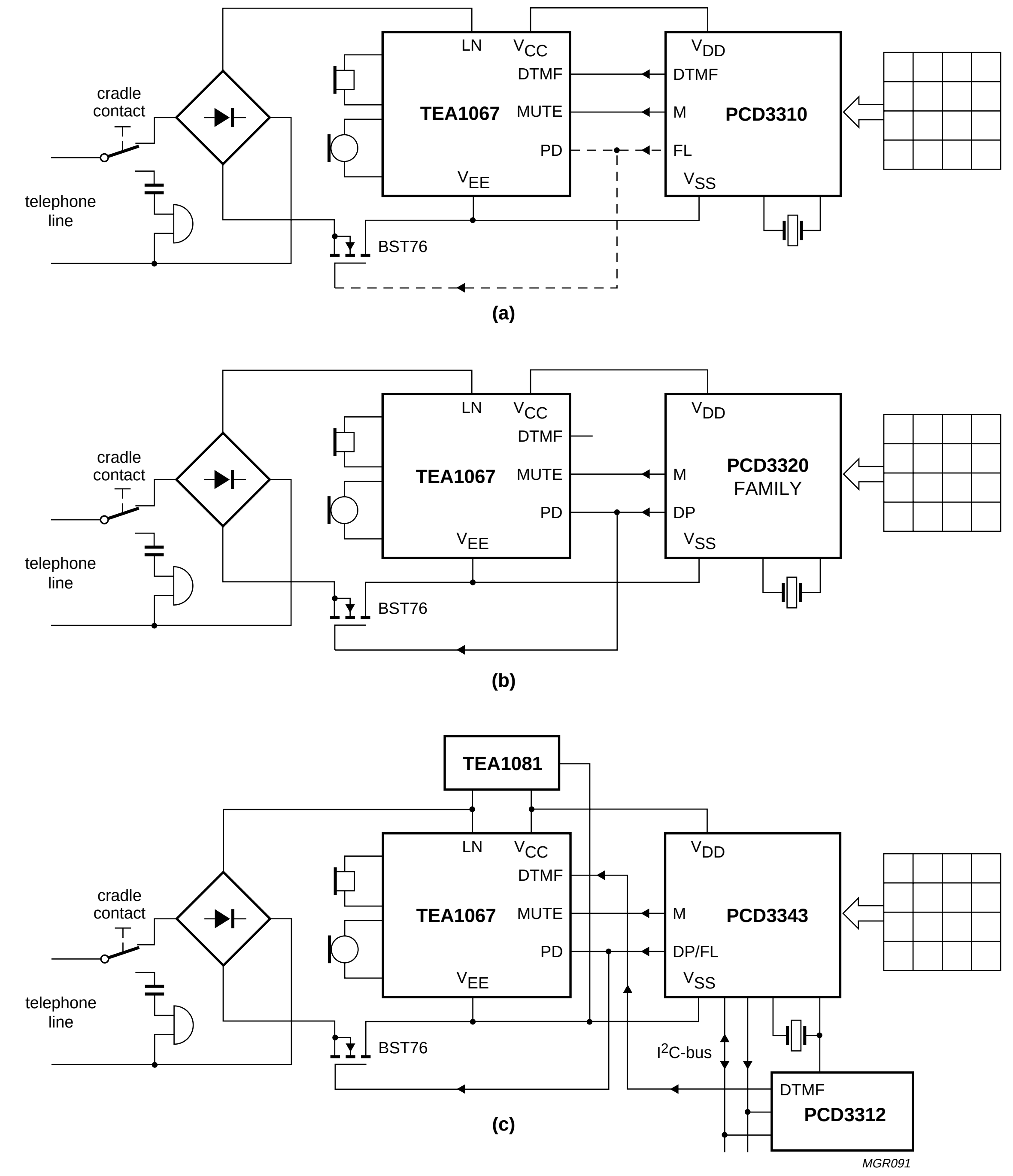
Fig.15 Test circuit for defining voltage gain of the receiving amplifier.

APPLICATION INFORMATION



The bridge to the left, the zener diode and R10 limit the current into the circuit and the voltage across the circuit during line transients. Pulse dialling or register recall require a different protection arrangement.
The DC line voltage can be set to a higher value by the resistor R_{VA} (REG to SLPE).

Fig.16 Typical application of the TEA1067, shown here with a piezoelectric earpiece and DTMF dialling.



(a) DTMF-Pulse set with CMOS dialling circuit PCD3310.
The dashed lines show an optional flash (register recall by timed loop break).

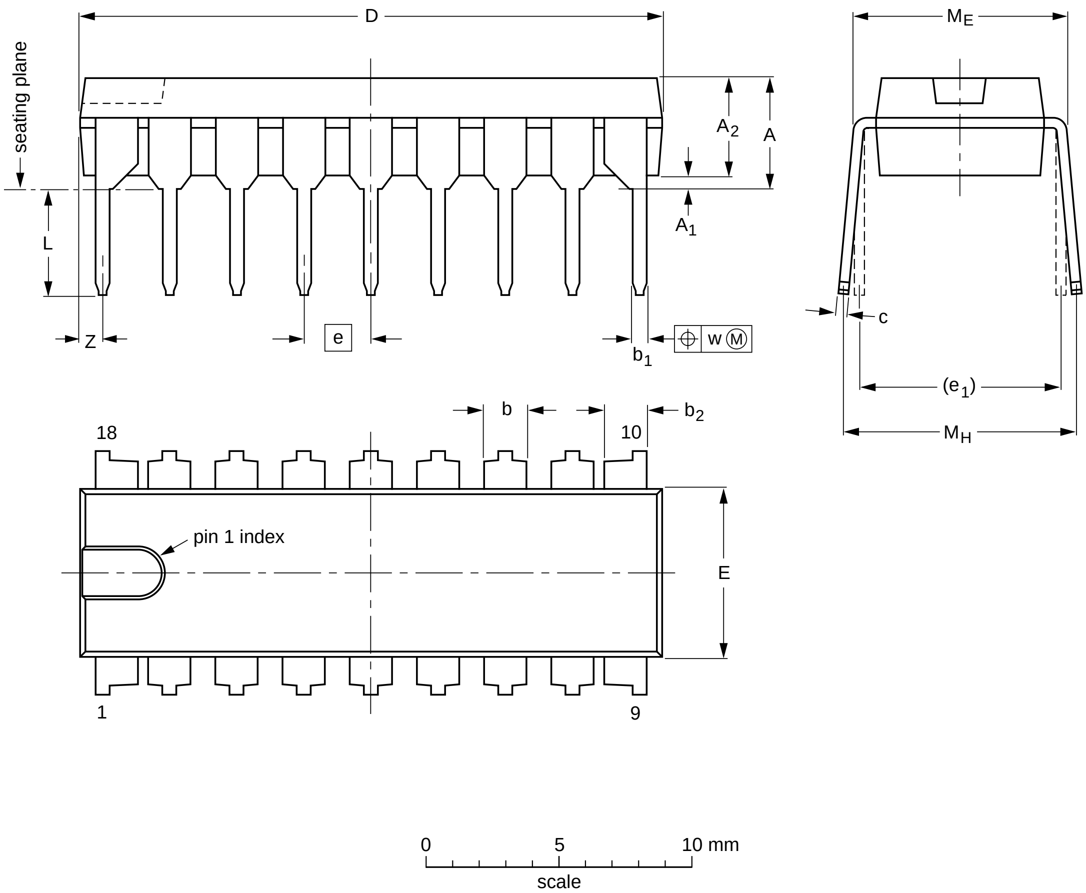
(b) Pulse dial set with one of the PCD3320 family of CMOS interrupted current-loop dialling circuits.

(c) Dual-standard (pulse and DTMF) feature phone with the PCD3343 CMOS controller and the PCD3312 CMOS DTMF generator with I^2C-bus. Supply is provided by the TEA1081 supply circuit.

Fig.17 Typical applications of the TEA1067 (simplified).

PACKAGE OUTLINES

DIP18: plastic dual in-line package; 18 leads (300 mil) SOT102-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

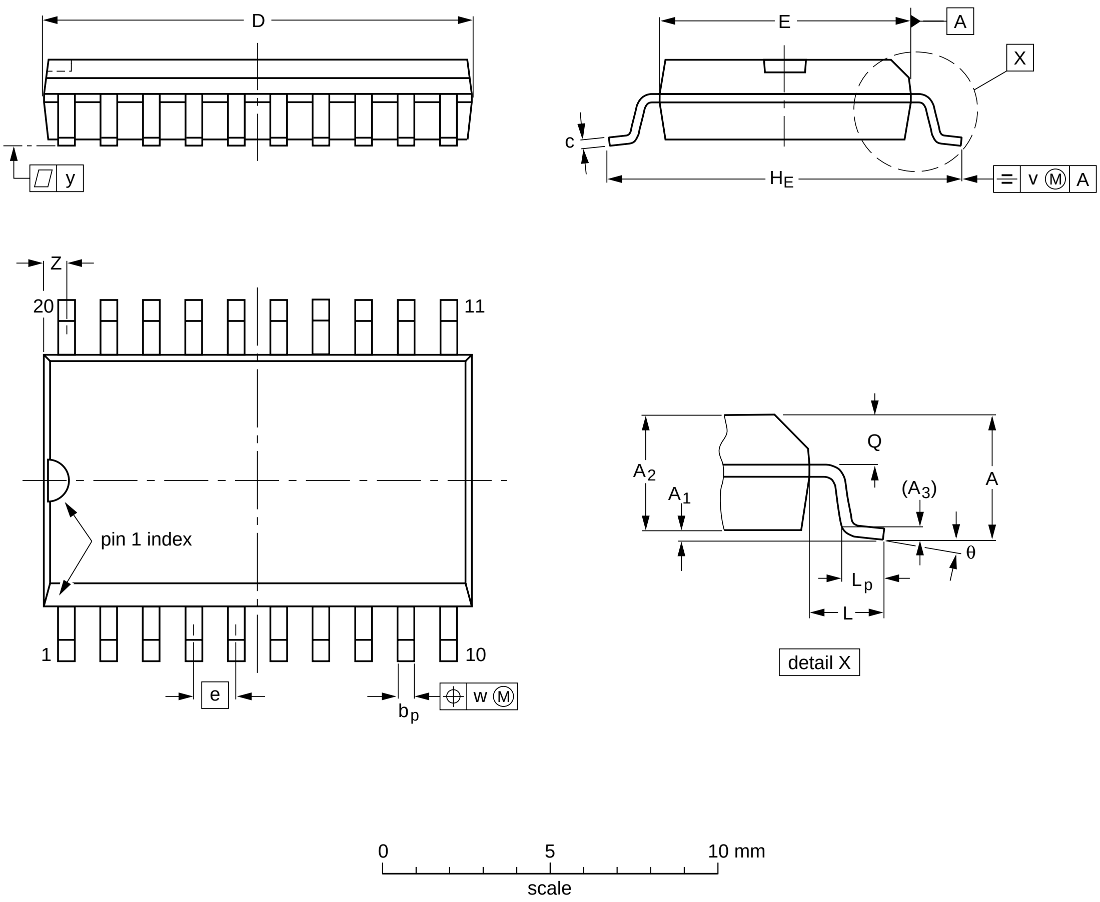
UNIT	A max.	A_1 min.	A_2 max.	b	b_1	b_2	c	D [(1)]	E [(1)]	e	e_1	L	M_E	M_H	w	Z [(1)] max.
mm	4.7	0.51	3.7	1.40 1.14	0.53 0.38	1.40 1.14	0.32 0.23	21.8 21.4	6.48 6.20	2.54	7.62	3.9 3.4	8.25 7.80	9.5 8.3	0.254	0.85
inches	0.19	0.020	0.15	0.055 0.044	0.021 0.015	0.055 0.044	0.013 0.009	0.86 0.84	0.26 0.24	0.10	0.30	0.15 0.13	0.32 0.31	0.37 0.33	0.01	0.033

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT102-1						~~93-10-14~~ 95-01-23

SO20: plastic small outline package; 20 leads; body width 7.5 mm **SOT163-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	2.65	0.30 0.10	2.45 2.25	0.25	0.49 0.36	0.32 0.23	13.0 12.6	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8^o 0^o
inches	0.10	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.51 0.49	0.30 0.29	0.050	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT163-1	075E04	MS-013AC				~~95-01-24~~ 97-05-22

SOLDERING

Introduction

There is no soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and surface mounted components are mixed on one printed-circuit board. However, wave soldering is not always suitable for surface mounted ICs, or for printed-circuits with high population densities. In these situations reflow soldering is often used.

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (order code 9398 652 90011).

DIP

SOLDERING BY DIPPING OR BY WAVE

The maximum permissible temperature of the solder is 260 °C; solder at this temperature must not be in contact with the joint for more than 5 seconds. The total contact time of successive solder waves must not exceed 5 seconds.

The device may be mounted up to the seating plane, but the temperature of the plastic body must not exceed the specified maximum storage temperature ($T_{stg\ max}$). If the printed-circuit board has been pre-heated, forced cooling may be necessary immediately after soldering to keep the temperature within the permissible limit.

REPAIRING SOLDERED JOINTS

Apply a low voltage soldering iron (less than 24 V) to the lead(s) of the package, below the seating plane or not more than 2 mm above it. If the temperature of the soldering iron bit is less than 300 °C it may remain in contact for up to 10 seconds. If the bit temperature is between 300 and 400 °C, contact may be up to 5 seconds.

SO

REFLOW SOLDERING

Reflow soldering techniques are suitable for all SO packages.

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several techniques exist for reflowing; for example, thermal conduction by heated belt. Dwell times vary between 50 and 300 seconds depending on heating method. Typical reflow temperatures range from 215 to 250 °C.

Preheating is necessary to dry the paste and evaporate the binding agent. Preheating duration: 45 minutes at 45 °C.

WAVE SOLDERING

Wave soldering techniques can be used for all SO packages if the following conditions are observed:

- A double-wave (a turbulent wave with high upward pressure followed by a smooth laminar wave) soldering technique should be used.
- The longitudinal axis of the package footprint must be parallel to the solder flow.
- The package footprint must incorporate solder thieves at the downstream end.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Maximum permissible solder temperature is 260 °C, and maximum duration of package immersion in solder is 10 seconds, if cooled to less than 150 °C within 6 seconds. Typical dwell time is 4 seconds at 250 °C.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

REPAIRING SOLDERED JOINTS

Fix the component by first soldering two diagonally-opposite end leads. Use only a low voltage soldering iron (less than 24 V) applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C. When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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Argentina: see South America

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Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213, Tel. +43 160 1010, Fax. +43 160 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6, 220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773

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Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor, 51 James Bourchier Blvd., 1407 SOFIA, Tel. +359 2 689 211, Fax. +359 2 689 102

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Denmark: Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S, Tel. +45 32 88 2636, Fax. +45 31 57 0044

Finland: Sinikalliontie 3, FIN-02630 ESPOO, Tel. +358 9 615800, Fax. +358 9 61580920

France: 51 Rue Carnot, BP317, 92156 SURESNES Cedex, Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427

Germany: Hammerbrookstraße 69, D-20097 HAMBURG, Tel. +49 40 23 53 60, Fax. +49 40 23 536 300

Greece: No. 15, 25th March Street, GR 17778 TAVROS/ATHENS, Tel. +30 1 4894 339/239, Fax. +30 1 4814 240

Hungary: see Austria

India: Philips INDIA Ltd, Band Box Building, 2nd floor, 254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025, Tel. +91 22 493 8541, Fax. +91 22 493 0966

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Ireland: Newstead, Clonskeagh, DUBLIN 14, Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053, TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

Italy: PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3, 20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557

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Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905, Tel. +9-5 800 234 7381

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United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes, MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421

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